

# **isc Silicon NPN Power Transistor**

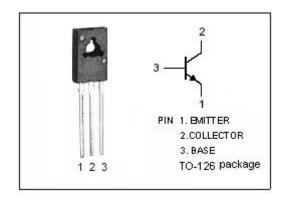
2SD2583

## **DESCRIPTION**

- High Collector Current-I<sub>C</sub>= 5A
- · Low Saturation Voltage -
  - :  $V_{CE(sat)}$ = 0.15V(Max)@  $I_{C}$ =1A,  $I_{B}$ = 50mA
- · High DC Current Gain-
  - : h<sub>FE</sub>= 150~600@ I<sub>C</sub>= 1A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

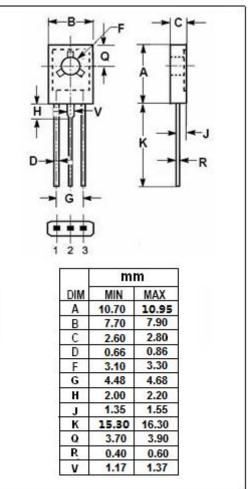
## **APPLICATIONS**

 Designed for audio frequency amplifier and switching applications.



## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	30	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V	
lc	Collector Current-Continuous	5.0	Α	
Icp	Collector Current-Pulse	10	Α	
I <sub>B</sub>	Base Current-Continuous	2.0	А	
Pc	Collector Power Dissipation @ T <sub>a</sub> =25°C	1.0		
	Collector Power Dissipation @ Tc=25°C	10	W	
TJ	Junction Temperature 150		$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range -55		$^{\circ}$ C	





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### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 50mA			0.15	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	Ic= 2A; I <sub>B</sub> = 0.1A			0.25	V
V <sub>CE(sat)-3</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.2A			0.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.1A			1.5	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 30V; I <sub>E</sub> = 0			0.1	μ <b>А</b>
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0			0.1	μ <b>Α</b>
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 2V	150		600	
h <sub>FE-2</sub>	DC Current Gain	Ic= 4A; Vc== 2V	50			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 50mA ; V <sub>CE</sub> = 10V		120		MHz
Сов	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V, f <sub>test</sub> = 1MHz		77		pF

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